

L Number	Hits	Search Text	DB	Time stamp
3	1423	silicon near1 precursor	USPAT; US-PGPUB; EPO; JPO	2004/10/01 10:01
4	188	(silicon near1 precursor) with (cvd (chemical near1 vapor near1 deposition))	USPAT; US-PGPUB; EPO; JPO	2004/10/01 10:03
5	11	((silicon near1 precursor) with (cvd (chemical near1 vapor near1 deposition)) and (low near1 k near1 dielectric))	USPAT; US-PGPUB; EPO; JPO	2004/10/01 10:03
6	17	((silicon near1 precursor) with (cvd (chemical near1 vapor near1 deposition)) and (low near1 k))	USPAT; US-PGPUB; EPO; JPO	2004/10/01 09:29
7	17	((silicon near1 precursor) with (cvd (chemical near1 vapor near1 deposition)) and (omcts octamethylcyclotetrasiloxane tmcts tetramethylcyclotetrasiloxane))	USPAT; US-PGPUB; EPO; JPO	2004/10/01 09:36
8	5	((silicon near1 precursor) with (cvd (chemical near1 vapor near1 deposition)) and (omcts octamethylcyclotetrasiloxane tmcts tetramethylcyclotetrasiloxane)) and (low near1 k)	USPAT; US-PGPUB; EPO; JPO	2004/10/01 09:36
9	0	20040156987.URPN.	USPAT	2004/10/01 09:32
10	1	"20040101633"	USPAT; US-PGPUB; EPO; JPO	2004/10/01 09:36
11	1	"20040101633" and (omcts octamethylcyclotetrasiloxane tmcts tetramethylcyclotetrasiloxane)	USPAT; US-PGPUB; EPO; JPO	2004/10/01 10:04
12	1	("20040101633" and (omcts octamethylcyclotetrasiloxane tmcts tetramethylcyclotetrasiloxane)) and (low near1 k)	USPAT; US-PGPUB; EPO; JPO	2004/10/01 09:37
13	1	((("20040101633" and (omcts octamethylcyclotetrasiloxane tmcts tetramethylcyclotetrasiloxane)) and (low near1 k)) and precursor	USPAT; US-PGPUB; EPO; JPO	2004/10/01 09:37
14	1	((("20040101633" and (omcts octamethylcyclotetrasiloxane tmcts tetramethylcyclotetrasiloxane)) and (low near1 k)) and precursor) and (cvd (chemical near1 vapor near1 deposition))	USPAT; US-PGPUB; EPO; JPO	2004/10/01 09:48
15	1	((("20040101633" and (omcts octamethylcyclotetrasiloxane tmcts tetramethylcyclotetrasiloxane)) and (low near1 k)) and precursor) and (cvd (chemical near1 vapor near1 deposition)) and (cvd (chemical near1 vapor near1 deposition))	USPAT; US-PGPUB; EPO; JPO	2004/10/01 09:49
16	1	((("20040101633" and (omcts octamethylcyclotetrasiloxane tmcts tetramethylcyclotetrasiloxane)) and (low near1 k)) and precursor) and (cvd (chemical near1 vapor near1 deposition)) and (cmp (chemical near1 mechanical near1 polishing))	USPAT; US-PGPUB; EPO; JPO	2004/10/01 10:04
17	0	(silicon near1 precursor) and ((((("20040101633" and (omcts octamethylcyclotetrasiloxane tmcts tetramethylcyclotetrasiloxane)) and (low near1 k)) and precursor) and (cvd (chemical near1 vapor near1 deposition)) and (cmp (chemical near1 mechanical near1 polishing)))	USPAT; US-PGPUB; EPO; JPO	2004/10/01 10:00
18	1	((("20040101633" and (omcts octamethylcyclotetrasiloxane tmcts tetramethylcyclotetrasiloxane)) and (low near1 k)) and precursor) and (cvd (chemical near1 vapor near1 deposition)) and (cmp (chemical near1 mechanical near1 polishing))) and precursor	USPAT; US-PGPUB; EPO; JPO	2004/10/01 10:01

19	842	(silicon near1 precursor) and (cvd (chemical near1 vapor near1 deposition))	USPAT; US-PGPUB; EPO; JPO	2004/10/01 10:03
20	74	((silicon near1 precursor) and (cvd (chemical near1 vapor near1 deposition))) and (low near1 dielectric)	USPAT; US-PGPUB; EPO; JPO	2004/10/01 10:04
21	18	((((silicon near1 precursor) and (cvd (chemical near1 vapor near1 deposition))) and (low near1 dielectric)) and (cmp (chemical near1 mechanical near1 polishing)))	USPAT; US-PGPUB; EPO; JPO	2004/10/01 10:04
22	8	((((silicon near1 precursor) and (cvd (chemical near1 vapor near1 deposition))) and (low near1 dielectric)) and (cmp (chemical near1 mechanical near1 polishing))) and (omcts octamethylcyclotetrasiloxane tmcts tetramethylcyclotetrasiloxane)	USPAT; US-PGPUB; EPO; JPO	2004/10/01 10:05
23	1	6287990.pn.	USPAT; US-PGPUB; EPO; JPO	2004/10/01 10:55
24	1	6287990.pn. and (low near1 dielectric)	USPAT; US-PGPUB; EPO; JPO	2004/10/01 10:55